

**/ Descriptions**

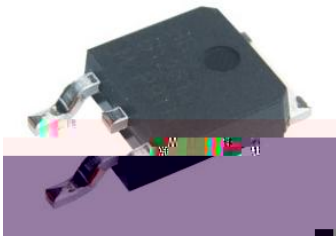
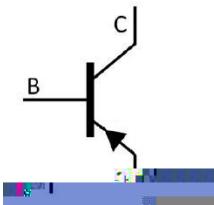
KF \$ , )      GE G      Silicon PNP transistor in a TO-252 Plastic Package.

**/ Features**

D 9

High breakdown voltage, adoption of MBIT process excellent  $h_{FE}$  linearity

High voltage driver applications.

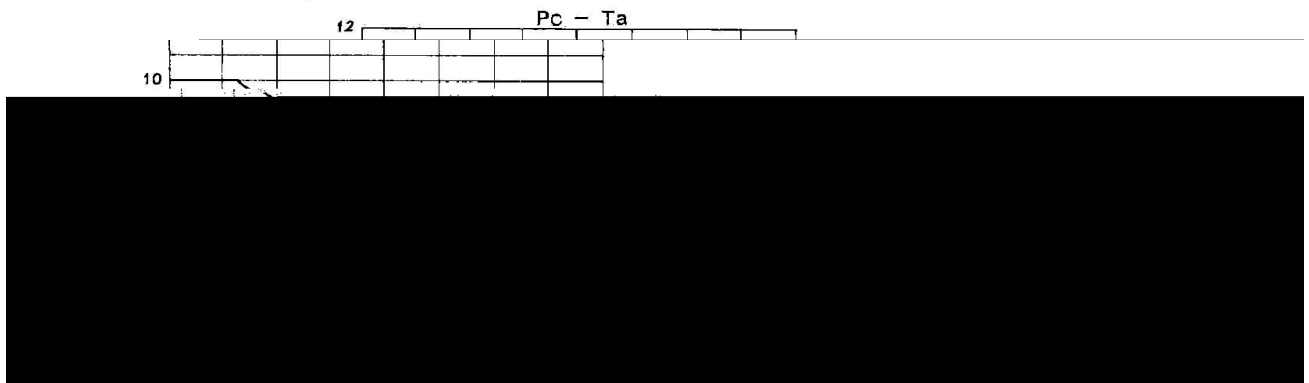
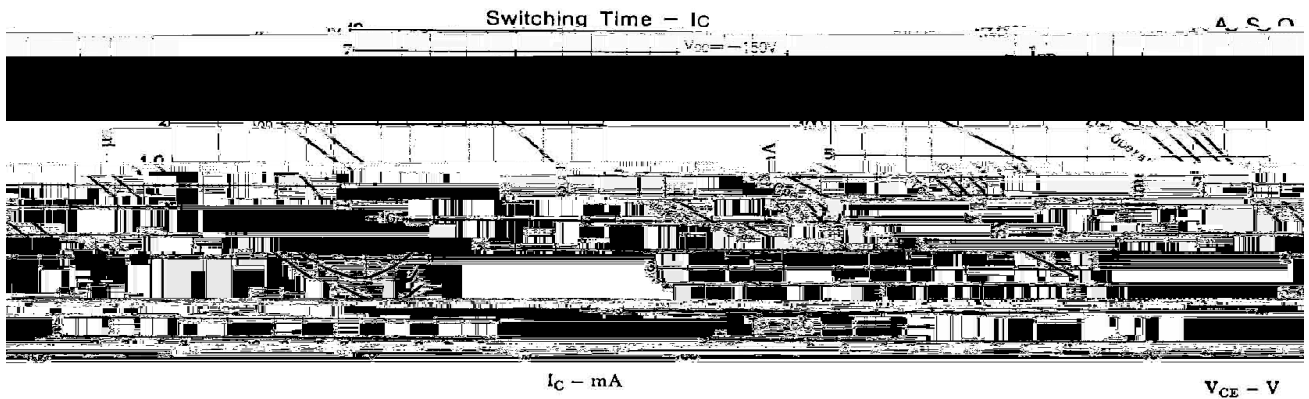
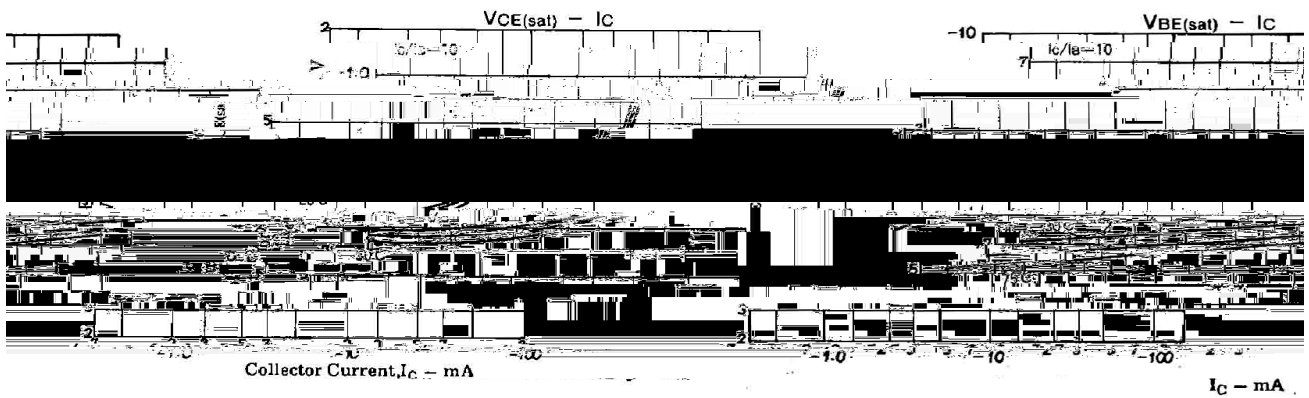
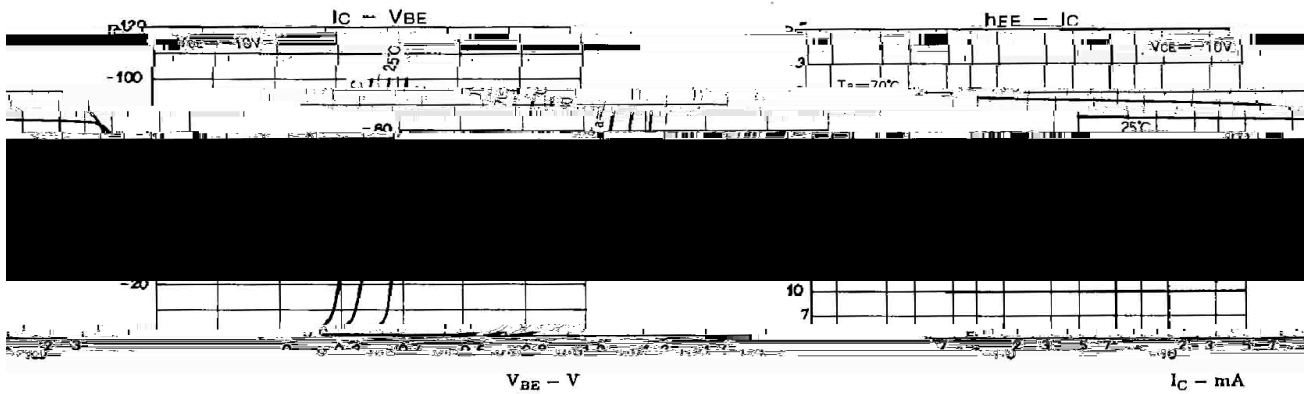


PIN1 Base      PIN 2,4 Collector      PIN 3 Emitter

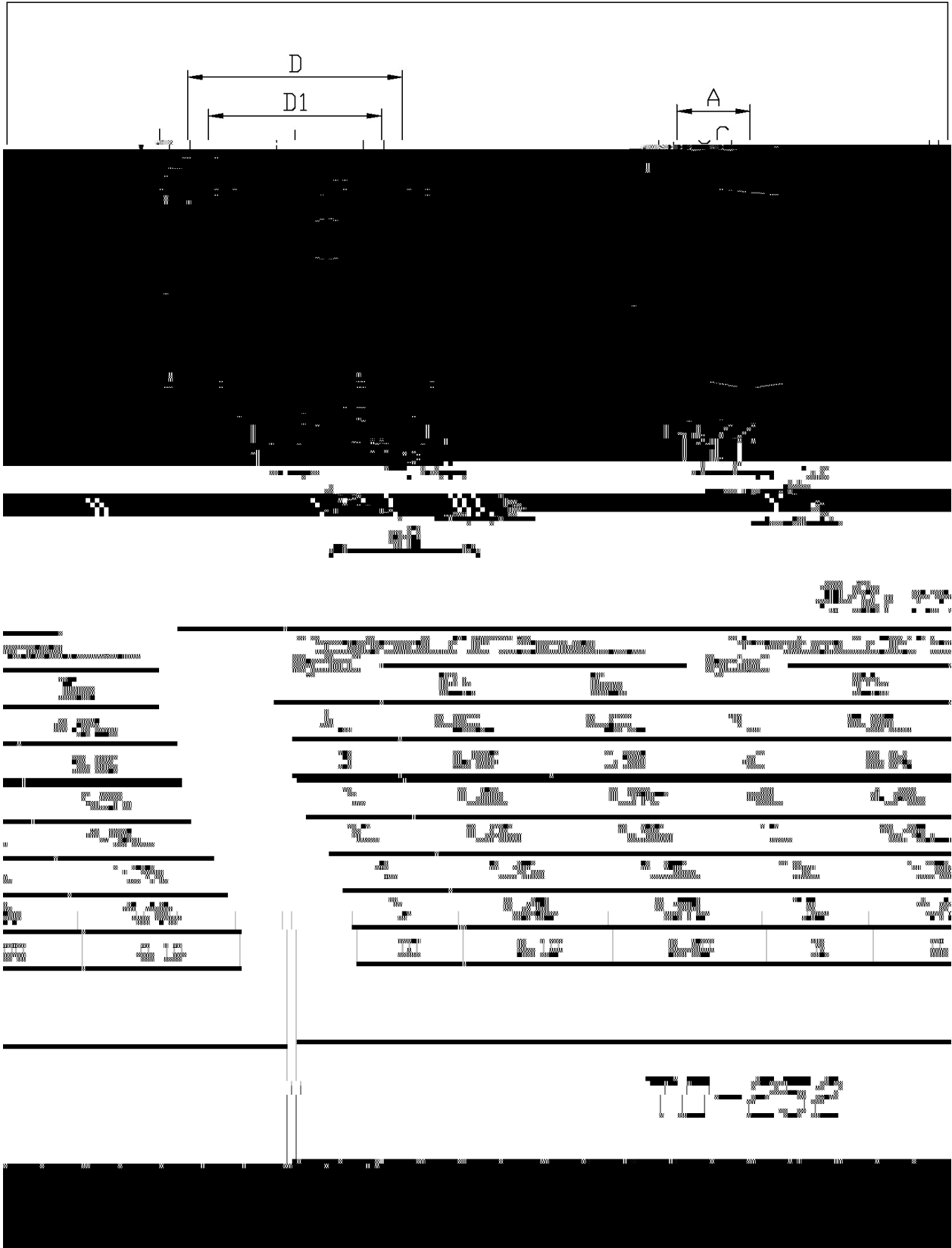
**/  $h_{FE}$  Classifications & Marking**

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	-400	V

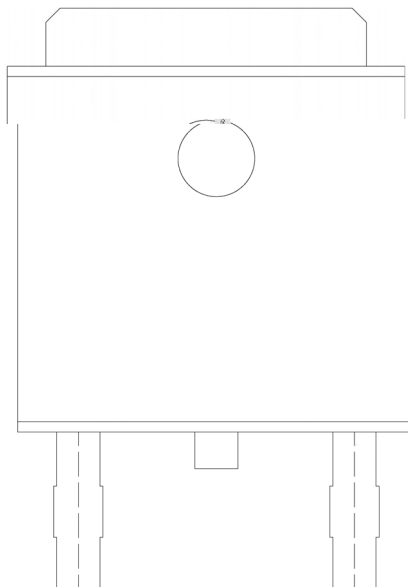
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

A1700

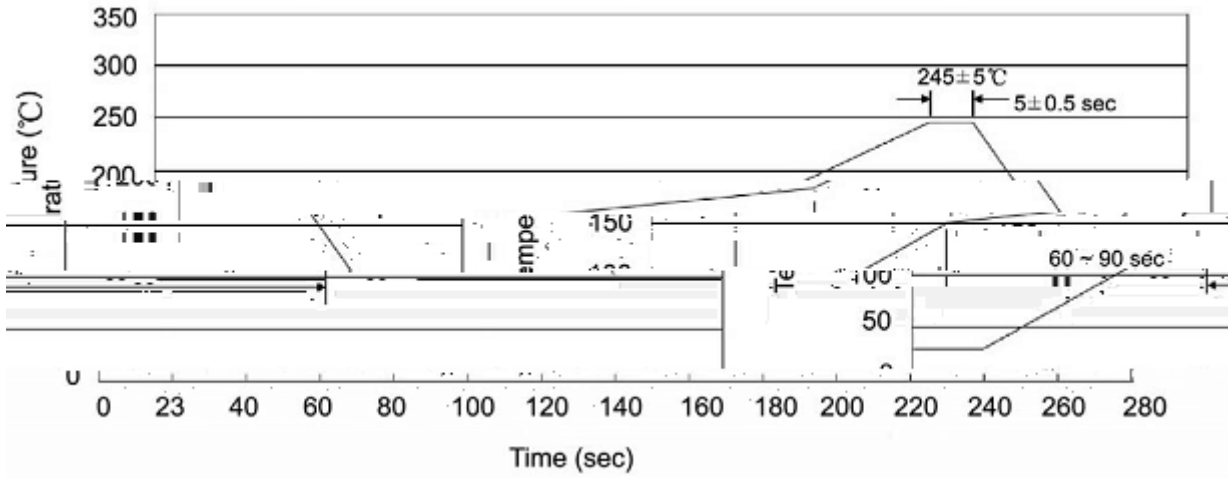
D1  $h_{FE}$

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Note:

BR: A13( )TjZmparyWFO

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- |   |        |     |            |          |   |
|---|--------|-----|------------|----------|---|
| 1 | 25     | 150 | 60         | 90sec;   | 1.Preheating:25~150 , Time:60~90sec.      |
| 2 | 245..5 |     | 5..0.5sec; |          | 2.Peak Temp.:245..5 , Duration:5..0.5sec. |
| 3 |        |     | 2          | 10 /sec. | 3. Cooling Speed: 2~10 /sec.              |

/ Resistance to Soldering Heat Test Conditions

260..5                      10..1 sec.                      Temp.:260±5                      Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units				Dimension	(unit mm <sup>3</sup> )
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box		